BCR12PM-14

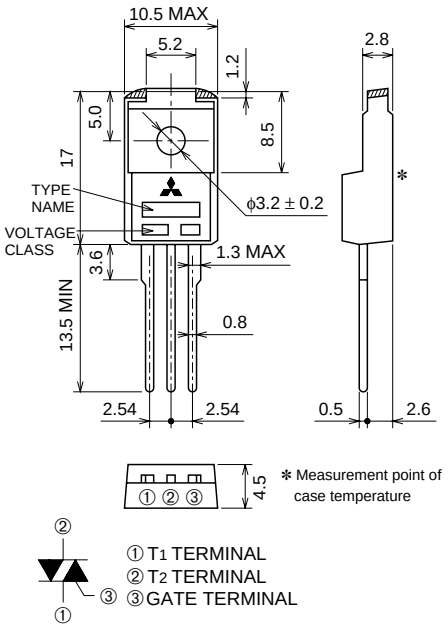
MEDIUM POWER USE

INSULATED TYPE, PLANAR PASSIVATION TYPE

BCR12PM-14

- $I_{T\ (RMS)}$ 12A
- V_{DRM} 700V
- $I_{FGT\ I}$, $I_{RGT\ I}$, $I_{RGT\ III}$ 30mA
- V_{iso} 1500V
- UL Recognized: File No. E80276

OUTLINE DRAWING Dimensions in mm



TO-220F

APPLICATION

Switching mode power supply, light dimmer, electric flasher unit, hair driver,
control of household equipment such as TV sets · stereo · refrigerator · washing machine · infrared kotatsu · carpet, solenoid drivers, small motor control,
copying machine, electric tool

MAXIMUM RATINGS

Symbol	Parameter	Voltage class	Unit
		14	
V_{DRM}	Repetitive peak off-state voltage *1	700	V
V_{DSM}	Non-repetitive peak off-state voltage *1	840	V

Symbol	Parameter	Conditions	Ratings	Unit
$I_{T\ (RMS)}$	RMS on-state current	Commercial frequency, sine full wave 360° conduction, T_c=74°C	12	A
I_{TSM}	Surge on-state current	60Hz sinewave 1 full cycle, peak value, non-repetitive	120	A
I^2t	I^2t for fusing	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current	60	A^2s
P_{GM}	Peak gate power dissipation		5	W
$P_{G\ (AV)}$	Average gate power dissipation		0.5	W
V_{GM}	Peak gate voltage		10	V
I_{GM}	Peak gate current		2	A
T_j	Junction temperature		–40 ~ +125	°C
T_{stg}	Storage temperature		–40 ~ +125	°C
—	Weight	Typical value	2.0	g
V_{iso}	Isolation voltage	T_a=25°C, AC 1 minute, T_1 · T_2 · G terminal to case	1500	V

*1. Gate open.

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MEDIUM POWER USE
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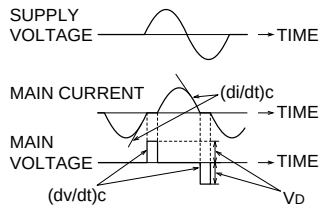
ELECTRICAL CHARACTERISTICS

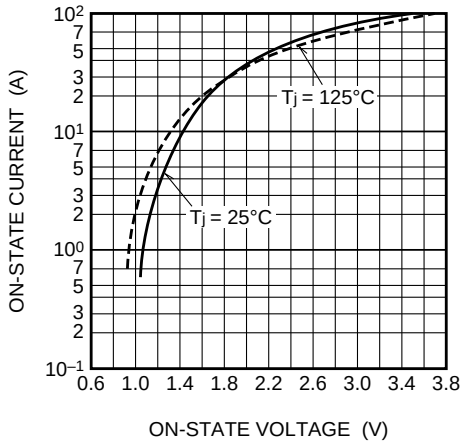
Symbol	Parameter		Test conditions	Limits			Unit
				Min.	Typ.	Max.	
I_{DRM}	Repetitive peak off-state current		T_j=125°C, V_{DRM} applied	—	—	2.0	mA
V_{TM}	On-state voltage		T_C=25°C, I_{TM}=20A, Instantaneous measurement	—	—	1.6	V
$V_{FGT\ I}$	Gate trigger voltage *2	I	T_j=25°C, V_D=6V, R_L=6Ω, R_G=330Ω	—	—	1.5	V
$V_{RGT\ I}$		II		—	—	1.5	V
$V_{RGT\ III}$		III		—	—	1.5	V
$I_{FGT\ I}$	Gate trigger current *2	I	T_j=25°C, V_D=6V, R_L=6Ω, R_G=330Ω	—	—	30	mA
$I_{RGT\ I}$		II		—	—	30	mA
$I_{RGT\ III}$		III		—	—	30	mA
V_{GD}	Gate non-trigger voltage		T_j=125°C, V_D=1/2V_{DRM}	0.2	—	—	V
$R_{th\ (j-c)}$	Thermal resistance		Junction to case *4	—	—	3.5	°C/W
$(dv/dt)_c$	Critical-rate of rise of off-state commutating voltage			*3	—	—	V/µs

*2. Measurement using the gate trigger characteristics measurement circuit.
*3. The critical-rate of rise of the off-state commutating voltage is shown in the table below.
*4. The contact thermal resistance $R_{th\ (c-f)}$ in case of greasing is 0.5°C/W.

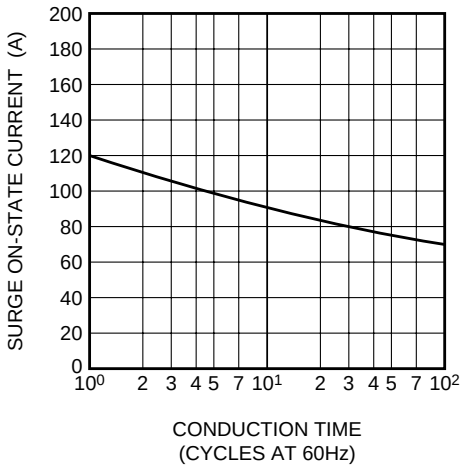
Voltage class	V_{DRM} (V)	$(dv/dt)_c$			Test conditions	Commutating voltage and current waveforms (inductive load)
		Symbol	Min.	Unit		
14	700	R	—	V/µs	1. Junction temperature T_j=125°C 2. Rate of decay of on-state commutating current $(di/dt)_c$=–6.0A/ms 3. Peak off-state voltage V_D=400V	
		L	10			

PERFORMANCE CURVES

MAXIMUM ON-STATE CHARACTERISTICS



RATED SURGE ON-STATE CURRENT



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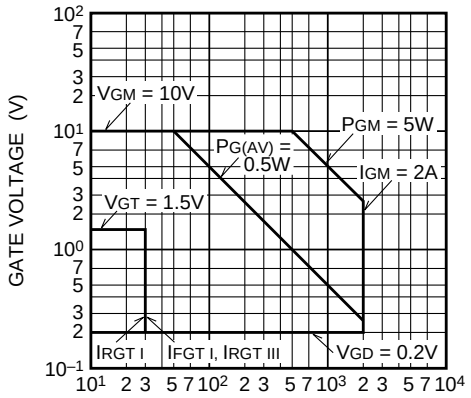
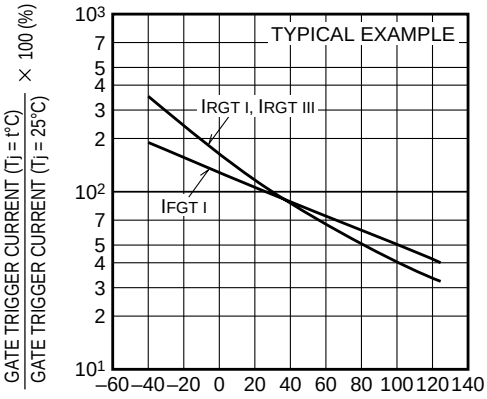
MEDIUM POWER USE
INSULATED TYPE, PLANAR PASSIVATION TYPE

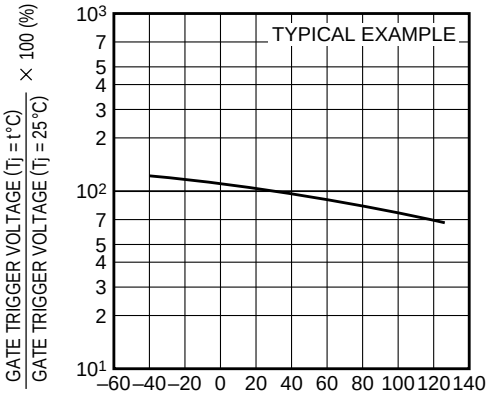
GATE CHARACTERISTICS



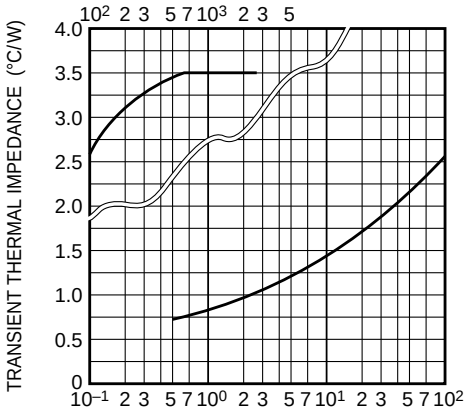
GATE TRIGGER CURRENT VS. JUNCTION TEMPERATURE



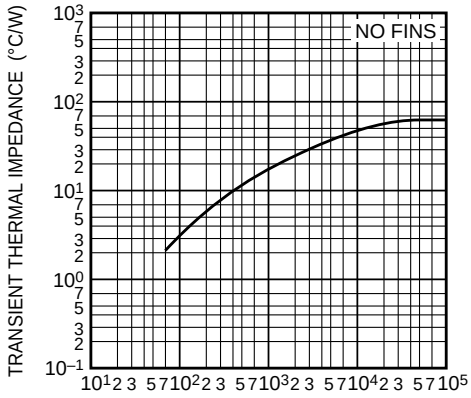
GATE TRIGGER VOLTAGE VS. JUNCTION TEMPERATURE



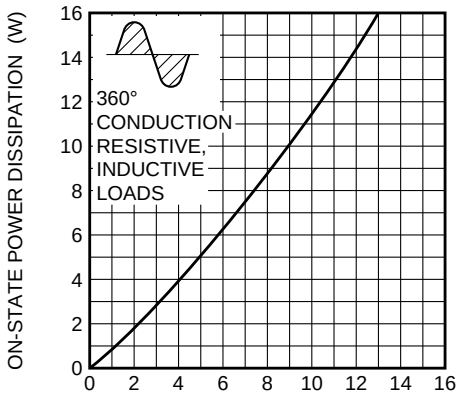
MAXIMUM TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (JUNCTION TO CASE)



MAXIMUM TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (JUNCTION TO AMBIENT)



MAXIMUM ON-STATE POWER DISSIPATION



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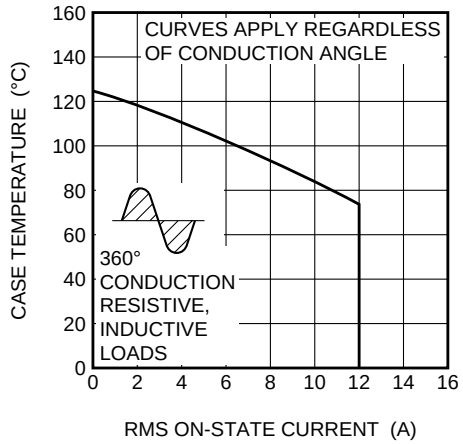
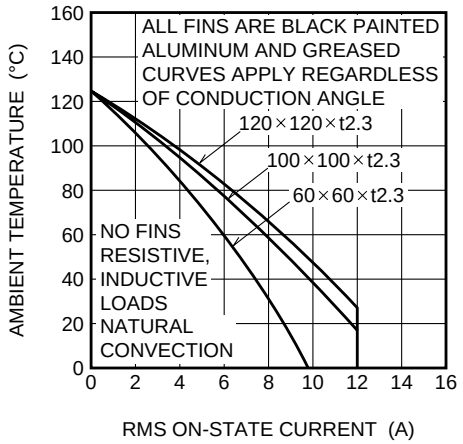
MEDIUM POWER USE
INSULATED TYPE, PLANAR PASSIVATION TYPE

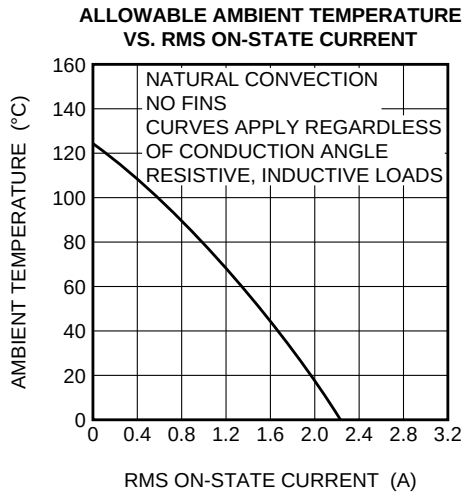
ALLOWABLE CASE TEMPERATURE VS. RMS ON-STATE CURRENT



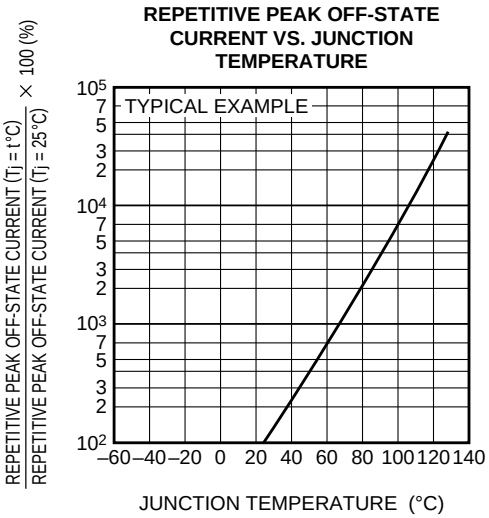
ALLOWABLE AMBIENT TEMPERATURE VS. RMS ON-STATE CURRENT



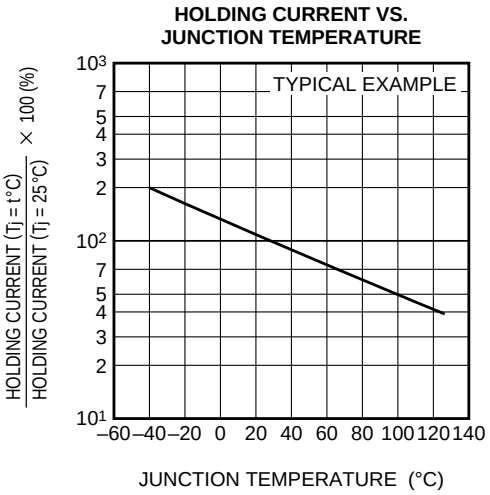
ALLOWABLE AMBIENT TEMPERATURE VS. RMS ON-STATE CURRENT



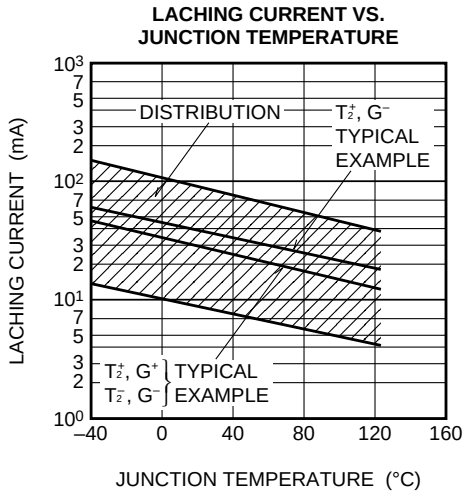
REPETITIVE PEAK OFF-STATE CURRENT VS. JUNCTION TEMPERATURE



HOLDING CURRENT VS. JUNCTION TEMPERATURE



LACHING CURRENT VS. JUNCTION TEMPERATURE



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MEDIUM POWER USE
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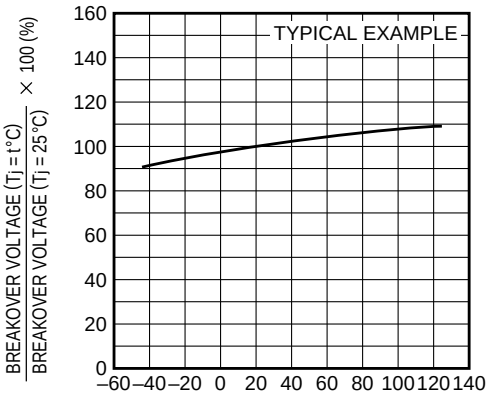
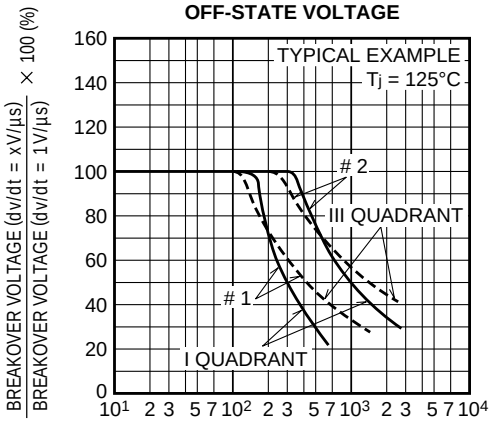
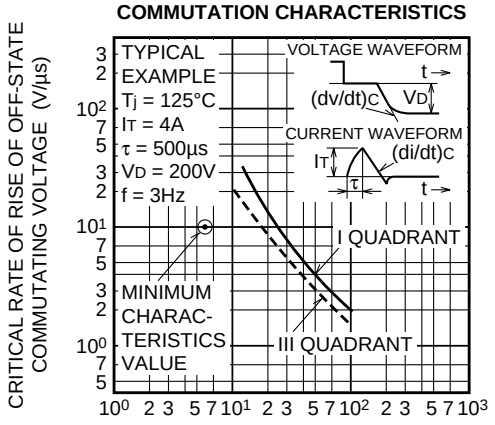
BREAKOVER VOLTAGE VS. JUNCTION TEMPERATURE



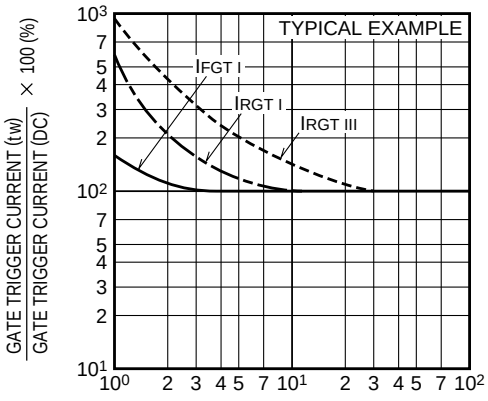
BREAKOVER VOLTAGE VS. RATE OF RISE OF OFF-STATE VOLTAGE



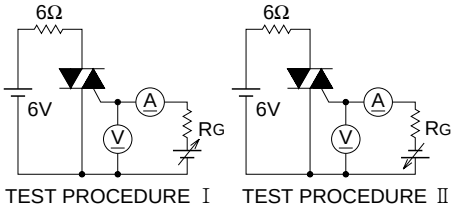
COMMUTATION CHARACTERISTICS

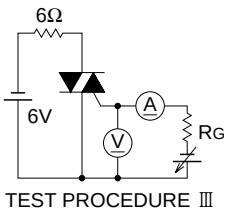


GATE TRIGGER CURRENT VS. GATE CURRENT PULSE WIDTH



GATE TRIGGER CHARACTERISTICS TEST CIRCUITS





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